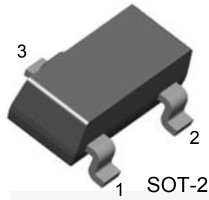
November 2014

BC817 / BC818
NPN Epitaxial Silicon Transistor

Features

- Switching and Amplifier Applications
- Suitable for AF-Driver Stages and Low Power Output Stages
- Complement to BC807 / BC808



SOT-23

1. Base 2. Emitter 3. Collector

Ordering Information(1)

Part Number	Marking	Package	Packing Method
BC81716MTF	8FA	SOT-23 3L	Tape and Reel
BC81725MTF	8FB	SOT-23 3L	Tape and Reel
BC81740MTF	8FC	SOT-23 3L	Tape and Reel
BC81816MTF	8GA	SOT-23 3L	Tape and Reel
BC81825MTF	8GB	SOT-23 3L	Tape and Reel
BC81840MTF	8GC	SOT-23 3L	Tape and Reel

Note:

1. Affix “-16,-25,-40” means h_{FE} classification. Affix “-M” means the matte type package. Affix “-TF” means the tape and reel type packing.

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at T_A = 25°C unless otherwise noted.

Symbol	Parameter		Value	Unit
V_{CBO}	Collector-Base Voltage	BC817	50	V
		BC818	30	
V_{CEO}	Collector-Emitter Voltage	BC817	45	V
		BC818	25	
V_{EBO}	Emitter-Base Voltage		5	V
I_C	Collector Current (DC)		800	mA
T_J	Junction Temperature		150	°C
T_{STG}	Storage Temperature		-65 to +150	°C